BGU7003W

Wideband silicon germanium low-noise amplifier MMIC

Rev. 2 — 11 April 2013

Product data sheet

1. Product profile

1.1 General description

The BGU7003W MMIC is a wideband amplifier in SiGe:C technology for high speed, low-noise applications in a plastic, leadless 6 pin, extremely thin small outline SOT886 package.

Table 1. Application information

 T_{amb} = 25 °C; V_{CC} = 2.85 V; $I_{CC(tot)}$ = 3.2 mA [1]; $V_{ENABLE} \ge 0.7$ V; f = 100 MHz; Z_S = Z_L = 50 Ω unless otherwise specified. All measurements are done with the SMA-connectors as reference plane.

Application	NF	S ₂₁ ²	RL_{in}	RLout	P _{i(1dB)}	P _{L(1dB)}	IP3 _I	IP3 _O
	(dB)	(dB)	(dB)	(dB)	(dBm)	(dBm)	(dBm)	(dBm)
high-ohmic FM LNA	1.2	13	0.5	16.5	-23	-11	-15 ^[2]	-2 [2]

^[1] $I_{CC(tot)} = I_{CC} + I_{RF_OUT} + I_{R_BIAS}$.

1.2 Features and benefits

- Low noise high gain microwave MMIC
- Applicable between 40 MHz and 6 GHz
- Integrated temperature stabilized bias for easy design
- Bias current configurable with external resistor
- 110 GHz transit frequency SiGe:C technology
- Power-down mode current consumption < 1 μA</p>
- ESD protection > 1 kV Human Body Model (HBM) on all pins

1.3 Applications

- GPS
- FM LNA
- Low-noise amplifiers for microwave communications systems
- WLAN and CDMA applications
- Analog / digital cordless applications



^[2] The third order intercept point is measured at -30 dBm per tone at RF_IN ($f_1 = 100$ MHz; $f_2 = 100.2$ MHz)

Wideband silicon germanium low-noise amplifier MMIC

2. Pinning information

Table 2. Pinning

Table 2.	ı ııııııg		
Pin	Description	Simplified outline	Graphic symbol
1	R_BIAS	0 5	
2	RF_IN	6 5 4	5 6
3	GND		2———4
4	RF_OUT		
5	ENABLE	1 2 3	1 3 sym128
6	V _{CC}	1 2 3 Transparent top view	J,

3. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BGU7003W	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1.45 \times 0.5 mm	SOT886		

4. Marking

Table 4. Marking codes

Type number	Marking code
BGU7003W	UW

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage	RF input AC coupled		-	3.0	V
I _{CC(tot)}	total supply current	configurable with external resistor		-	25	mΑ
P _{tot}	total power dissipation	T _{sp} ≤ 103 °C	[1]	-	70	mW
T _{stg}	storage temperature			-65	+150	°C
Tj	junction temperature			-	150	°C

^[1] T_{sp} is the temperature at the solder point of the ground lead.

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point		235	K/W

BGU7003W

All information provided in this document is subject to legal disclaimers.

© NXP B.V. 2013. All rights reserved.

Wideband silicon germanium low-noise amplifier MMIC

7. Characteristics

Table 7. Characteristics

 T_{amb} = 25 °C; V_{CC} = 2.5 V; $I_{CC(tot)}$ = 5.0 mA; V_{ENABLE} \geq 0.7 V unless otherwise specified. All measurements done on characterization board without matching, de-embedded up to the pins.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{CC}	supply voltage	RF input AC coupled		2.2	-	2.85	V
I _{CC(tot)}	total supply current	configurable with external resistor	[1]	3	-	15	mA
		$V_{\text{ENABLE}} \leq 0.4 \text{ V}$	<u>[1]</u>	-	-	0.001	mA
T _{amb}	ambient temperature			-40	+25	+85	°C
$ s_{21} ^2$	insertion power gain	T _{amb} = 25 °C					
		f = 100 MHz	[2]	21.0	22.5	-	dB
		f = 900 MHz	[2]	18.5	20.0	-	dB
		f = 1.575 GHz		16.0	17.5	-	dB
		f = 2.4 GHz	[2]	14.0	15.2	-	dB
		f = 5.8 GHz	[2]	10.0	11.4	-	dB
		$-40~^{\circ}\text{C} \le T_{amb} \le +85~^{\circ}\text{C}$					
		f = 100 MHz	[2]	20.0	22.5	-	dB
		f = 900 MHz	[2]	17.5	20.0	-	dB
		f = 1.575 GHz	[2]	15.0	17.5	-	dB
		f = 2.4 GHz	[2]	13.0	15.2	-	dB
		f = 5.8 GHz	[2]	9.0	11.4	-	dB
MSG	maximum stable gain	f = 100 MHz		-	33.8	-	dB
		f = 900 MHz		-	23.8	-	dB
		f = 1.575 GHz		-	20.5	-	dB
		f = 2.4 GHz		-	17.8	-	dB
		f = 5.8 GHz		-	15.4	-	dB
NF_{min}	minimum noise figure	f = 100 MHz		-	0.6	-	dB
		f = 900 MHz		-	0.6	-	dB
		f = 1.575 GHz		-	0.7	-	dB
		f = 2.4 GHz		-	0.8	-	dB
		f = 5.8 GHz		-	1.5	-	dB

^[1] $I_{CC(tot)} = I_{CC} + I_{RF_OUT} + I_{R_BIAS}$.

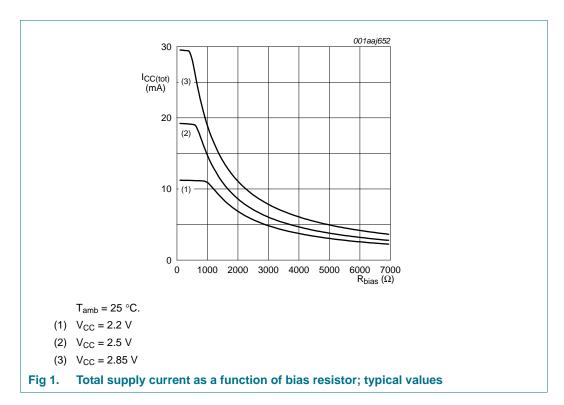
Table 8. ENABLE (pin 5)

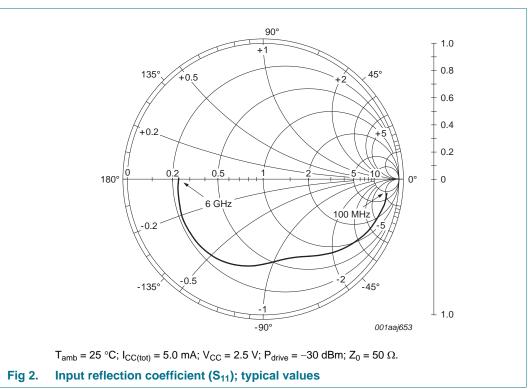
-40 °C ≤ T_{amb} ≤ +85 °C

V _{ENABLE} (V)	State
≤ 0.4	OFF
≥ 0.7	ON

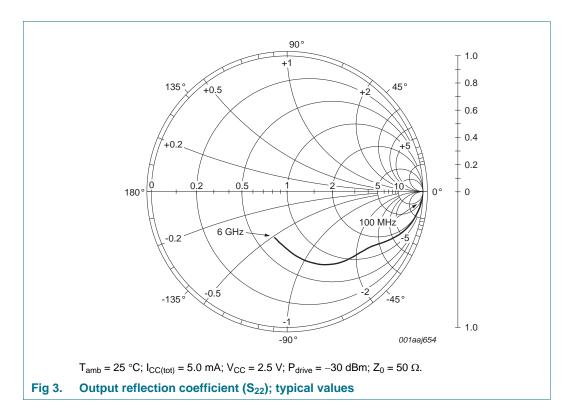
^[2] Guaranteed by design and characterization.

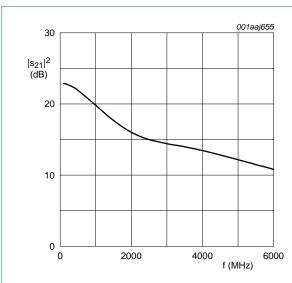
Wideband silicon germanium low-noise amplifier MMIC





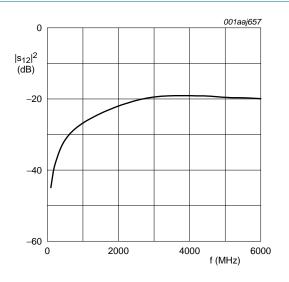
Wideband silicon germanium low-noise amplifier MMIC





 T_{amb} = 25 °C; $I_{CC(tot)}$ = 5.0 mA; V_{CC} = 2.5 V; P_{drive} = -30 dBm; Z_0 = 50 Ω .

Fig 4. Insertion power gain $(|s_{21}|^2)$ as a function of frequency; typical values

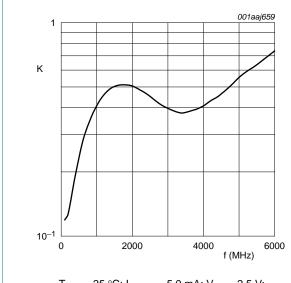


$$\begin{split} &T_{amb} = 25~^{\circ}\text{C}; \ I_{CC(tot)} = 5.0 \ \text{mA}; \ V_{CC} = 2.5 \ \text{V}; \\ &P_{drive} = -30 \ \text{dBm}; \ Z_0 = 50 \ \Omega. \end{split}$$

Fig 5. Isolation ($|s_{12}|^2$) as a function of frequency; typical values

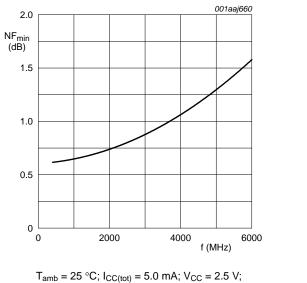
BGU7003W NXP Semiconductors

Wideband silicon germanium low-noise amplifier MMIC



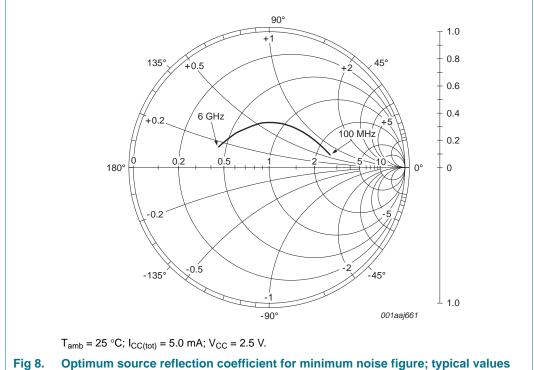
$$\begin{split} T_{amb} = 25~^{\circ}C;~I_{CC(tot)} = 5.0~\text{mA};~V_{CC} = 2.5~\text{V};\\ P_{drive} = -30~\text{dBm};~Z_0 = 50~\Omega. \end{split}$$

Rollet's stability factor as a function of Fig 6. frequency; typical values

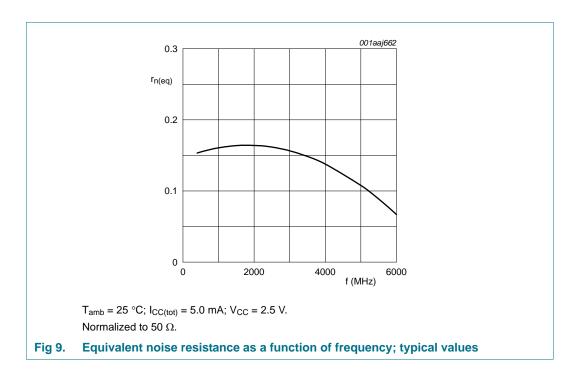


$$\begin{split} T_{amb} = 25~^{\circ}C; \ I_{CC(tot)} = 5.0 \ mA; \ V_{CC} = 2.5 \ V; \\ P_{drive} = -30 \ dBm; \ Z_0 = 50 \ \Omega. \end{split}$$

Minimum noise figure as a function of Fig 7. frequency; typical values



Wideband silicon germanium low-noise amplifier MMIC



8. Application information

8.1 High-ohmic FM LNA

Table 9. Characteristics [1]

 T_{amb} = 25 °C; V_{CC} = 2.85 V; $I_{CC(tot)}$ = 3.2 mA [2]; $V_{ENABLE} \ge 0.7$ V; f = 100 MHz; Z_S = Z_L = 50 Ω unless otherwise specified. All measurements are done with the SMA-connectors as reference plane.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
NF	noise figure		-	1.2	-	dB
$ s_{21} ^2$	Insertion power gain		-	13	-	dB
RL_{in}	input return loss		-	0.5	-	dB
RL_{out}	output return loss		-	16.5	-	dB
$P_{i(1dB)} \\$	input power at 1 dB gain compression		-	-23	-	dBm
$P_{L(1dB)}$	output power at 1 dB gain compression		-	-11	-	dBm
IP3 _I	input third-order intercept point	<u> </u>	[3]	-15	-	dBm
IP3 _O	output third-order intercept point	<u>[</u>	[3]	-2	-	dBm

^[1] See application note: AN11034 for details.

^[2] $I_{CC(tot)} = I_{CC} + I_{RF_OUT} + I_{R_BIAS}$.

^[3] The third order intercept point is measured at -30 dBm per tone at RF_IN ($f_1 = 100$ MHz; $f_2 = 100.2$ MHz)

Wideband silicon germanium low-noise amplifier MMIC

8.2 50 ohm FM LNA

Table 10. Characteristics[1]

 T_{amb} = 25 °C; V_{CC} = 2.8 V; $I_{CC(tot)}$ = 4.3 mA [2]; V_{ENABLE} \geq 0.7 V; f = 100 MHz; Z_S = Z_L = 50 Ω (input and output matched to 50 Ω) unless otherwise specified. All measurements are done with the SMA-connectors as reference plane.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
NF	noise figure		-	1.5	-	dB
$ s_{21} ^2$	Insertion power gain		-	15	-	dB
RLin	input return loss		-	9	-	dB
RL _{out}	output return loss		-	14	-	dB
P _{i(1dB)}	input power at 1 dB gain compression		-	-20	-	dBm
P _{L(1dB)}	output power at 1 dB gain compression		-	-6	-	dBm
IP3 _I	input third-order intercept point		3] _	-12.5	-	dBm
IP3 _O	output third-order intercept point		3] _	2.5	-	dBm

^[1] See application note AN11035 for details.

^[2] $I_{CC(tot)} = I_{CC} + I_{RF_OUT} + I_{R_BIAS}$.

^[3] The third order intercept point is measured at -30 dBm per tone at RF_IN ($f_1 = 100$ MHz; $f_2 = 100.2$ MHz)

Wideband silicon germanium low-noise amplifier MMIC

9. Package outline

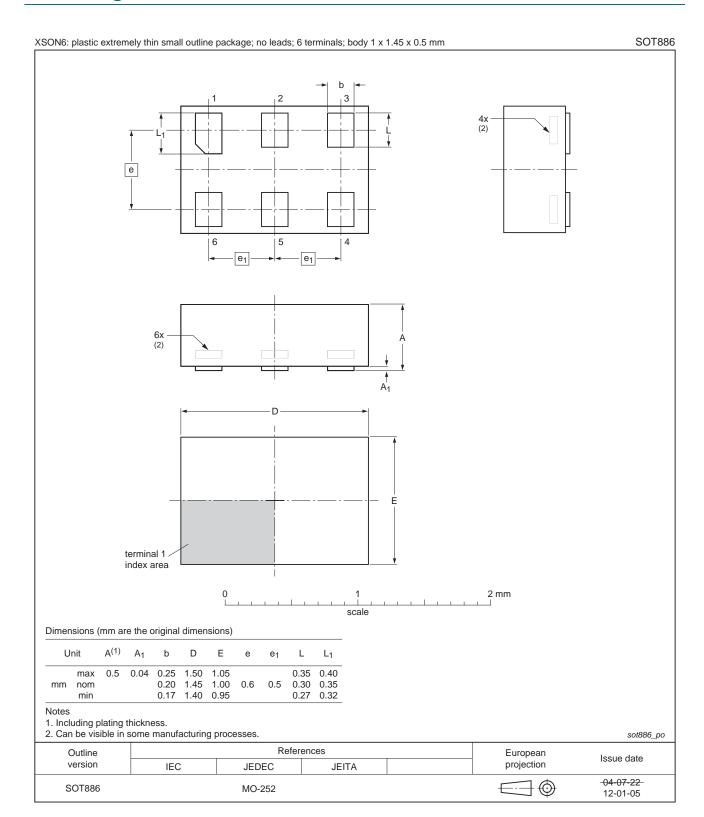


Fig 10. Package outline SOT886 (XSON6)

BGU7003W All information provided in this document is subject to legal disclaimers.

© NXP B.V. 2013. All rights reserved.

BGU7003W NXP Semiconductors

Wideband silicon germanium low-noise amplifier MMIC

10. Handling information

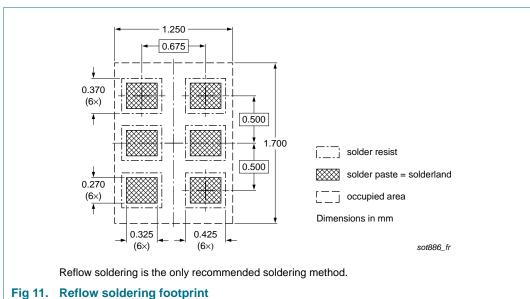
CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

11. Soldering



12. Abbreviations

Table 11. **Abbreviations**

Acronym	Description
AC	Alternating Current
CDMA	Code Division Multiple Access
DC	Direct Current
FM	Frequency Modulation
FR4	Flame Retardant 4
GPS	Global Positioning System
LNA	Low-Noise Amplifier
MMIC	Monolithic Microwave Integrated Circuit
RF	Radio Frequency
SiGe:C	Silicon Germanium Carbon
SMA	SubMiniature version A
WLAN	Wireless Local Area Network

Wideband silicon germanium low-noise amplifier MMIC

13. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
BGU7003W v.2	20130411	Product data sheet	-	BGU7003W v.1		
Modifications: • Figure 10 on page 9: figure has been updated.						
BGU7003W v.1	20110830	Product data sheet	-	-		

Wideband silicon germanium low-noise amplifier MMIC

14. Legal information

14.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

14.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

Product specification — The information and data provided in a Product data sheet shall define the specification of the product as agreed between NXP Semiconductors and its customer, unless NXP Semiconductors and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the NXP Semiconductors product is deemed to offer functions and qualities beyond those described in the Product data sheet.

14.3 Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information. NXP Semiconductors takes no responsibility for the content in this document if provided by an information source outside of NXP Semiconductors.

In no event shall NXP Semiconductors be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, NXP Semiconductors' aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of NXP Semiconductors.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors and its suppliers accept no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using NXP Semiconductors products, and NXP Semiconductors accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the NXP Semiconductors product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

NXP Semiconductors does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using NXP Semiconductors products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). NXP does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Terms and conditions of commercial sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nxp.com/profile/terms, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. NXP Semiconductors hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of NXP Semiconductors products by customer.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

BGU7003W

All information provided in this document is subject to legal disclaimers.

© NXP B.V. 2013. All rights reserved.

12 of 14

Wideband silicon germanium low-noise amplifier MMIC

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from competent authorities.

Non-automotive qualified products — Unless this data sheet expressly states that this specific NXP Semiconductors product is automotive qualified, the product is not suitable for automotive use. It is neither qualified nor tested in accordance with automotive testing or application requirements. NXP Semiconductors accepts no liability for inclusion and/or use of non-automotive qualified products in automotive equipment or applications.

In the event that customer uses the product for design-in and use in automotive applications to automotive specifications and standards, customer (a) shall use the product without NXP Semiconductors' warranty of the product for such automotive applications, use and specifications, and (b) whenever customer uses the product for automotive applications beyond

NXP Semiconductors' specifications such use shall be solely at customer's own risk, and (c) customer fully indemnifies NXP Semiconductors for any liability, damages or failed product claims resulting from customer design and use of the product for automotive applications beyond NXP Semiconductors' standard warranty and NXP Semiconductors' product specifications.

Translations — A non-English (translated) version of a document is for reference only. The English version shall prevail in case of any discrepancy between the translated and English versions.

14.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

15. Contact information

For more information, please visit: http://www.nxp.com

For sales office addresses, please send an email to: salesaddresses@nxp.com

Wideband silicon germanium low-noise amplifier MMIC

16. Contents

1	Product profile
1.1	General description 1
1.2	Features and benefits
1.3	Applications
2	Pinning information 2
3	Ordering information 2
4	Marking 2
5	Limiting values 2
6	Thermal characteristics 2
7	Characteristics 3
8	Application information 7
8.1	High-ohmic FM LNA 7
8.2	50 ohm FM LNA 8
9	Package outline 9
10	Handling information 10
11	Soldering 10
12	Abbreviations
13	Revision history 11
14	Legal information
14.1	Data sheet status
14.2	Definitions
14.3	Disclaimers
14.4	Trademarks13
15	Contact information
16	Contents

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for RF Amplifier category:

Click to view products by NXP manufacturer:

Other Similar products are found below:

A82-1 BGA622H6820XTSA1 BGA 728L7 E6327 BGB719N7ESDE6327XTMA1 HMC397-SX HMC405 HMC561-SX HMC8120-SX HMC8121-SX HMC-ALH382-SX HMC-ALH476-SX SE2433T-R SMA3101-TL-E SMA39 A66-1 A66-3 A67-1 LX5535LQ LX5540LL MAAM02350 HMC3653LP3BETR HMC549MS8GETR HMC-ALH435-SX SMA101 SMA32 SMA411 SMA531 SST12LP17E-XX8E SST12LP19E-QX6E WPM0510A HMC5929LS6TR HMC5879LS7TR HMC1126 HMC1087F10 HMC1086 HMC1016 SMA1212 MAX2689EWS+T MAAMSS0041TR MAAM37000-A1G LTC6430AIUF-15#PBF CHA5115-QDG SMA70-2 SMA4011 A231 HMC-AUH232 LX5511LQ LX5511LQ-TR HMC7441-SX HMC-ALH310